

## High Speed GaAlAs Infrared Emitter

# OPE5687HP

The **OPE5687HP** is GaAlAs infrared emitting diode that is designed for high power, low forward voltage and high speed rise / fall time. This device is optimized for speed and efficiency at emission wavelength 880nm and has a high radiant efficiency over a wide range of forward current. This device is packaged T1-3/4 package and has narrow beam angle with lensed package and cup frame. Especially this device is suited as the emitter of data transmission without cable.

### FEATURES

- Ultra high-speed : 25ns rise time
- 880nm wavelength
- Wide beam angle
- Low forward voltage
- High power and high reliability
- Available for pulse operating

### APPLICATIONS

- Emitter of IrDA
- IR Audio and Telephone
- High speed IR communication
- IR LANs
- Available for wireless digital data transmission

### STORAGE

- Condition : 5°C~35°C,R.H.60%
- Terms : within 3 months from production date
- Remark : Once the package is opened, the products should be used within a day. Otherwise, it should be keeping in a damp proof box with desiccants.

\* Please take proper steps in order to secure reliability and safety in required conditions and environments for this device.

### MAXIMUM RATINGS

(Ta=25°C)

Item	Symbol	Rating	Unit
Power Dissipation	P <sub>D</sub>	150	mW
Forward current	I <sub>F</sub>	100	mA
Pulse forward current *1	I <sub>FP</sub>	1.0	A
Reverse voltage	V <sub>R</sub>	4.0	V
Operating temp.	T <sub>opr.</sub>	-25~ +85	°C
Soldering temp. *2	T <sub>sol.</sub>	260.	°C

\*1. Duty ratio = 1/100, pulse width=0.1ms.

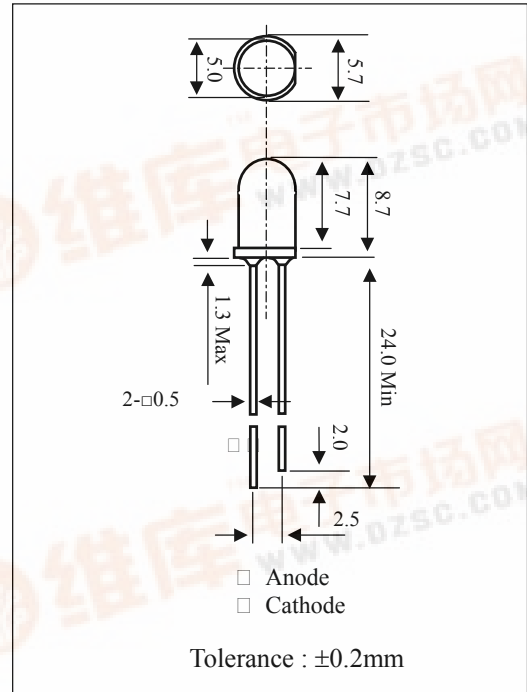
\*2. Lead Soldering Temperature (2mm from case for 5sec.).

### ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =50mA		1.5	2.0	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =4V			10	μA
Capacitance	C <sub>t</sub>	f=1MHz		20		□
Radiant intensity	I <sub>e</sub>	I <sub>F</sub> =50mA	25	50		mW/□
Power	P <sub>o</sub>	I <sub>F</sub> =100mA	20	35		mW
Peak emission wavelength	λ <sub>p</sub>	I <sub>F</sub> =50mA		880		nm
Spectral bandwidth 50% Half angle	Δλ	I <sub>F</sub> =50□		45		nm
	Δθ	I <sub>F</sub> =50□		±22		deg.
Optical rise & fall time(10%~90%)	tr/tf	I <sub>F</sub> =50□		25/15		ns
		I <sub>F</sub> =50mA DC				

DIMENSIONS(Unit : mm)



Tolerance : ±0.2mm

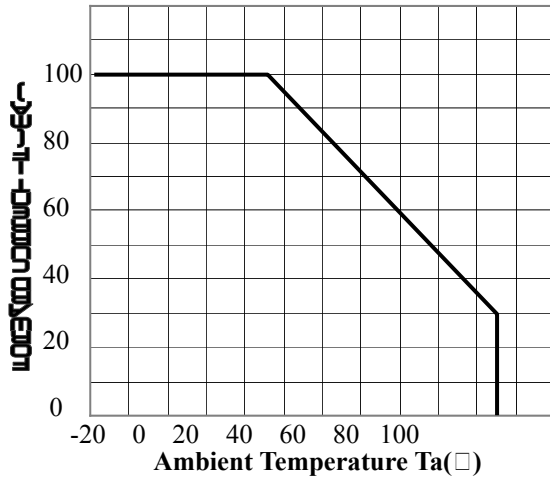


\*3.  $10\log(P_o(fc \text{ MHz})/P_o(0.1 \text{ MHz})) = -3$

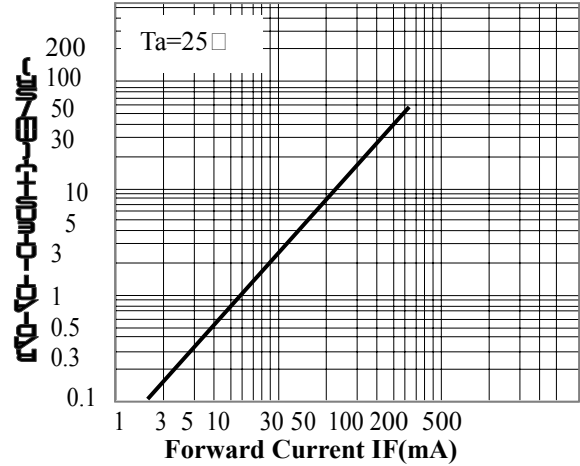
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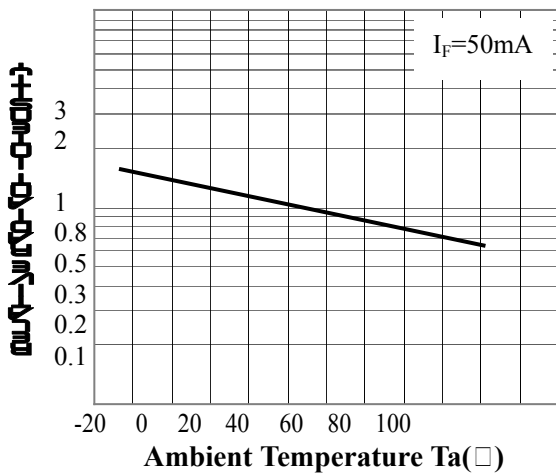
● FORWARD CURRENT Vs. AMBIENT TEMP.



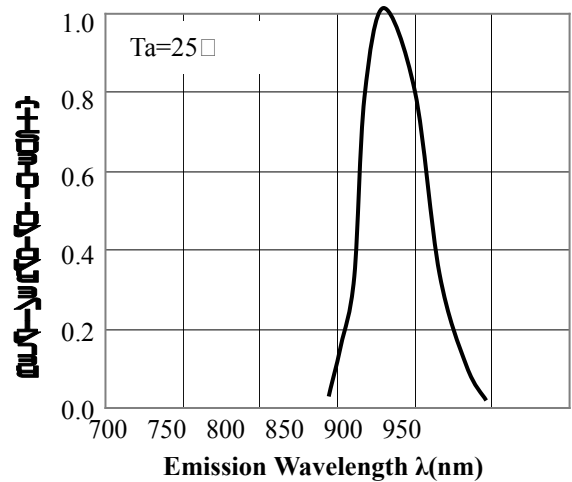
● RADIANT INTENSITY Vs. FORWARD CURRENT.



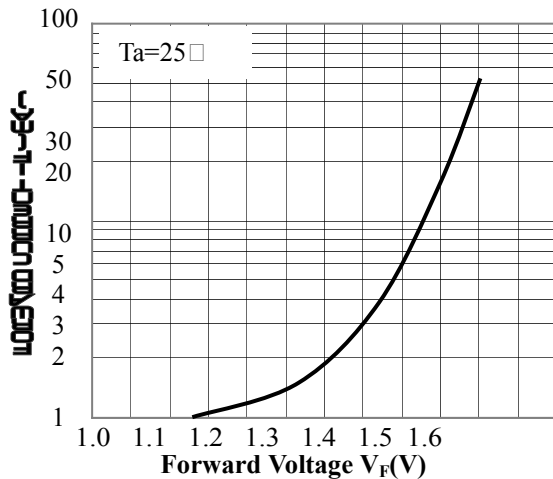
● RELATIVE RADIANT INTENSITY Vs. AMBIENT TEMP.



● RELATIVE RADIANT INTENSITY Vs. EMISSION WAVELENGTH.



● FORWARD CURRENT Vs. FORWARD VOLTAGE



● ANGULAR DISPLACEMENT Vs. RELATIVE RADIANT INTENSITY

